

1. (Amended) A wafer holding device adapted for use in an apparatus for treating a principal surface of a semiconductor wafer under a predetermined heating condition while the back surface of said principal surface of the wafer is held by the device at a predetermined position within a chamber of said apparatus, said device comprising:

B' a susceptor formed in the surface thereof with a wafer loading area for supporting the back surface of the wafer,

a plurality of support pins each arranged at one of four equiangularly spaced positions along a circumference of at least one concentric circle in said wafer loading area so as to protrude from the surface of said susceptor, and

a resilient mechanism made from at least one of quartz or SiC for supporting said support pins.

2. (Amended) The wafer holding device according to claim 1, wherein said support pins are disposed in positions which support the wafer along the crystal orientation $\langle 110 \rangle$ with respect to the crystal plane (100) of the wafer.

3. (Amended) The wafer holding device according to claim 1, wherein said resilient mechanism includes a plurality of flexible

members made from at least one of quartz or SiC each supporting one of said support pins.

4. (Amended) A wafer holding device adapted for use in an apparatus for treating a principal surface of a semiconductor wafer under a predetermined heating condition while the back surface of said principal surface of the wafer is held by the device at a predetermined position within a chamber of said apparatus, said device comprising:

a susceptor formed in the surface thereof with a wafer loading area for supporting the back surface of the wafer, and

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cont a plurality of support pins each arranged at one of four equiangularly spaced positions along a circumference of at least one concentric circle in said wafer loading area so as to protrude from the surface of said susceptor, each of said support pins including a resilient mechanism, wherein said resilient mechanism includes a plurality of flexible members each supporting one of said support pins,

wherein each said flexible member comprises a leaf spring made from at least one of quartz or SiC.

5. (Twice Amended) A wafer holding device adapted for use in an apparatus for treating a principal surface of a semiconductor

wafer under a predetermined heating condition while the back surface of said principal surface of the wafer is vertically or obliquely held by the device at a predetermined position within a chamber of said apparatus, said device comprising:

a substrate holder for supporting the back surface of said wafer thereon,

rotating means for circumferentially rotating said wafer along with the substrate holder, and

a plurality of holding members provided on said substrate holder and placed in contact with the peripheral edge of said wafer loaded thereon, said holding members including resilient means made from at least one of quartz or SiC and being adapted to act against said peripheral edge of said wafer to exert a holding force toward the center of said wafer in such degree that said wafer is prevented from coming off when said wafer is rotated along said substrate holder by said rotating means.

6. (Amended) The wafer holding device according to claim 5, wherein said substrate holder includes an inner wall surface disposed to face the peripheral edge of said wafer loaded on said substrate holder, and wherein said holding means includes a plurality of contact members for contacting with the peripheral edge of said wafer and a plurality of quartz spring members

disposed on said inner wall surface to apply an energizing force tending toward a center of said wafer to said contact members.

7. (Amended) The wafer holding device according to claim 5, wherein said substrate holder includes an inner wall surface disposed to face the peripheral edge of said wafer loaded on said substrate holder, and wherein said holding means includes inner-wall contact means including a part or a whole of a plurality of sections forming said inner wall surface and quartz spring means for energizing said inner-wall contact means toward a center of said wafer.

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cont 8. (Amended) A wafer holding device adapted for use in an apparatus for treating a principal surface of a semiconductor wafer under a predetermined heating condition while the back surface of said principal surface of the wafer is vertically or obliquely held by the device at a predetermined position within a chamber of said apparatus, said device comprising:

a substrate holder for supporting the back surface of said wafer thereon; and

rotating means for circumferentially rotating said wafer along with the substrate holder,

wherein said substrate holder includes periphery contact means for contacting with at least a portion of the back surface at the peripheral edge of said wafer loaded on said substrate holder,

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cont and wherein said holding means includes spring means made from at least one of quartz or SiC for contacting with a portion of the principal surface at the peripheral edge of said wafer loaded on said substrate holder and for clamping and holding said wafer between the same and said periphery contact means.
